



## DESCRIPTION

This NPN transistor is designed for general purpose amplifier applications. This device is housed in the SOT-723 package which is designed for low power surface mount applications, where board space is at a premium.

The 2SC5658QM~2SC5658RM are available in SOT-723 package

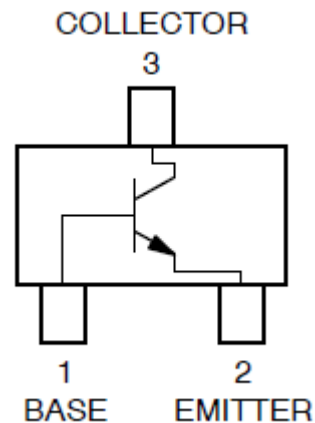
## ORDERING INFORMATION

| Package Type                             | Part Number    |
|------------------------------------------|----------------|
| SOT-723                                  | 2SC5658QM      |
|                                          | 2SC5658RM      |
| Note                                     | 4,000pcs/ Reel |
| AiT provides all RoHS Compliant Products |                |

## FEATURES

- Reduces Board Space
- High  $h_{FE}$ , 210~460 (typical)
- Low  $V_{CE(sat)}$ , < 0.5V
- ESD Performance:  
Human Body Model; > 2000V  
Machine Model; > 200V
- Available in SOT-723 package

## PIN DESCRIPTION





## ABSOLUTE MAXIMUM RATINGS

T<sub>A</sub>=25°C

|                                                     |                     |
|-----------------------------------------------------|---------------------|
| V <sub>(BR)CBO</sub> , Collector-Base Voltage       | 50Vdc               |
| V <sub>(BR)CEO</sub> , Collector-Emitter Voltage    | 50Vdc               |
| V <sub>(BR)EBO</sub> , Emitter-Base Voltage         | 5.0Vdc              |
| I <sub>C</sub> , Collector Current-Continuous       | 100mA <sub>dc</sub> |
| <b>THERMAL CHARACTERISTICS</b>                      |                     |
| P <sub>D</sub> , Power Dissipation <sup>NOTE1</sup> | 260mW               |
| T <sub>J</sub> , Junction Temperature               | 150°C               |
| T <sub>STG</sub> , Storage Temperature Range        | -55°C~+150°C        |

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

NOTE1: Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint.

## ELECTRICAL CHARACTERISTICS

T<sub>A</sub>=25°C

| Parameter                                             | Symbol               | Conditions                                                                        | Min. | Typ. | Max. | Unit |
|-------------------------------------------------------|----------------------|-----------------------------------------------------------------------------------|------|------|------|------|
| Collector-Base Breakdown Voltage                      | V <sub>(BR)CBO</sub> | I <sub>C</sub> = 50μA <sub>dc</sub> , I <sub>E</sub> = 0                          | 50   | -    | -    | Vdc  |
| Collector-Emitter Breakdown Voltage                   | V <sub>(BR)CEO</sub> | I <sub>C</sub> = 1.0mA <sub>dc</sub> , I <sub>B</sub> = 0                         | 50   | -    | -    | Vdc  |
| Emitter-Base Breakdown Voltage                        | V <sub>(BR)EBO</sub> | I <sub>E</sub> = 50μA <sub>dc</sub> , I <sub>E</sub> = 0                          | 5.0  | -    | -    | Vdc  |
| Collector-Base Cutoff Current                         | I <sub>CBO</sub>     | V <sub>CB</sub> = 30Vdc, I <sub>E</sub> = 0                                       | -    | -    | 0.5  | μA   |
| Emitter-Base Cutoff Current                           | I <sub>EBO</sub>     | V <sub>EB</sub> = 4.0Vdc, I <sub>B</sub> = 0                                      | -    | -    | 0.5  | μA   |
| Collector-Emitter Saturation Voltage <sup>NOTE2</sup> | V <sub>CE(sat)</sub> | I <sub>C</sub> = 50mA <sub>dc</sub> , I <sub>B</sub> = 5.0mA <sub>dc</sub>        | -    | -    | 0.4  | Vdc  |
| DC Current Gain <sup>NOTE2</sup>                      | 2SC5658QM            | h <sub>FE</sub><br>V <sub>CE</sub> = 6.0Vdc, I <sub>C</sub> = 1.0mA <sub>dc</sub> | 120  | -    | 270  | -    |
|                                                       | 2SC5658RM            |                                                                                   | 180  | -    | 390  | -    |
| Transition Frequency                                  | f <sub>T</sub>       | V <sub>CE</sub> = 12Vdc, I <sub>C</sub> = 2.0mA <sub>dc</sub> ,<br>f = 30MHz      | -    | 180  | -    | MHz  |
| Output Capacitance                                    | C <sub>OB</sub>      | V <sub>CB</sub> = 12Vdc, I <sub>C</sub> = 0A <sub>dc</sub> ,<br>f = 1.0MHz        | -    | 2.0  | -    | pF   |

NOTE2: Pulse Test: Pulse Width ≤ 300μs, D.C. ≤ 2%.



### TYPICAL CHARACTERISTICS

Figure 1.  $I_C - V_{CE}$

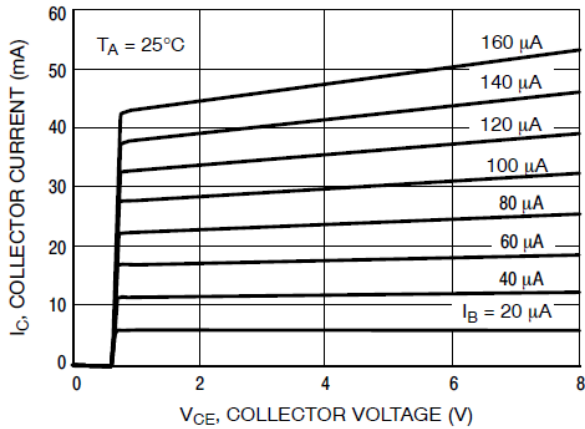


Figure 3. Base Emitter Saturation Voltage vs. Collector Current

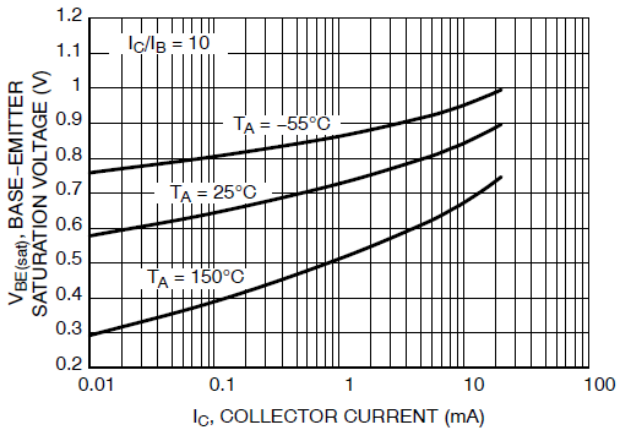


Figure 5. Saturation Region

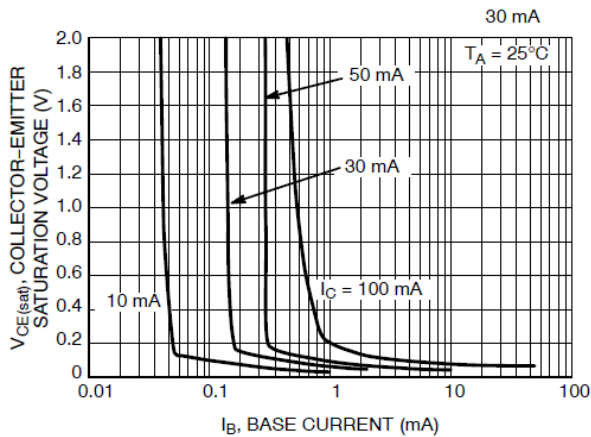


Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

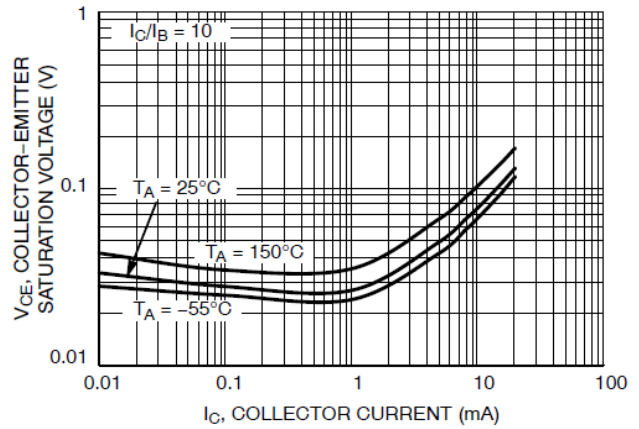


Figure 4. DC Current Gain vs. Collector Current

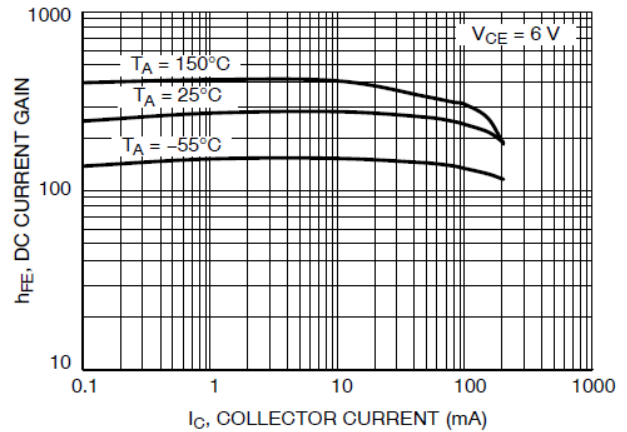


Figure 6. Base-Emitter Turn-ON Voltage vs. Collector Current

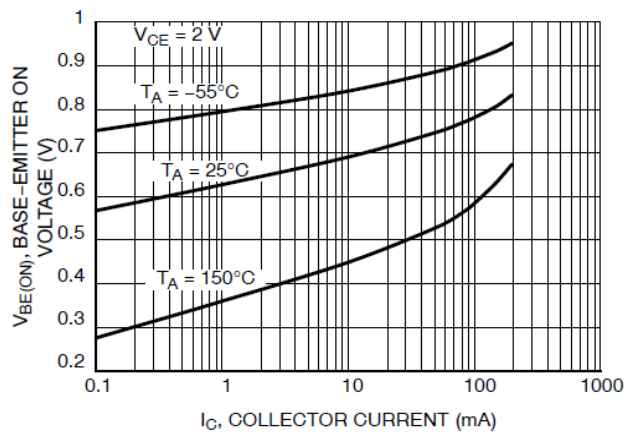




Figure 7. Capacitance

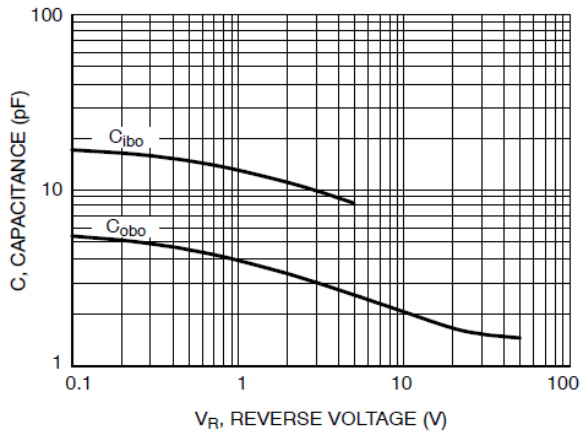


Figure 8. Current Gain Bandwidth Product vs. Collector Current

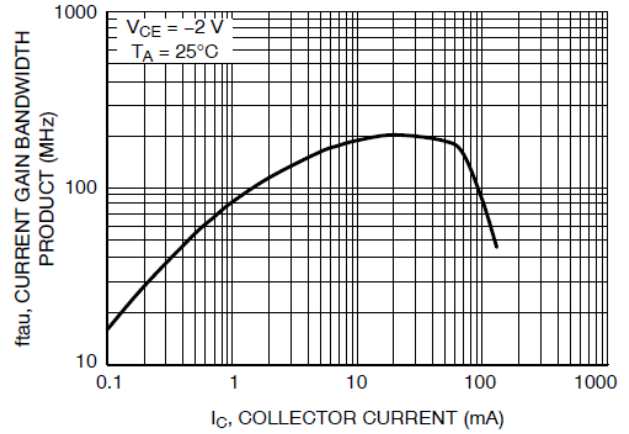
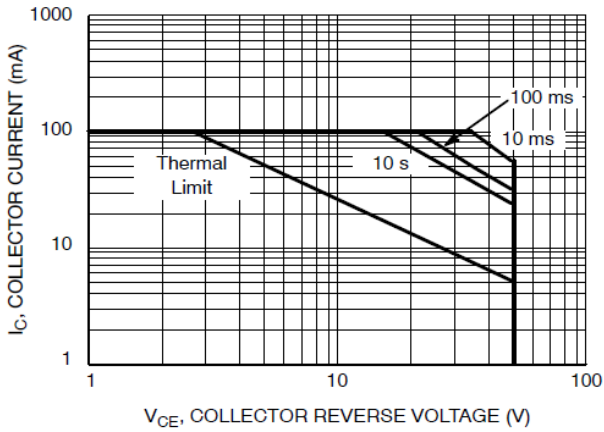


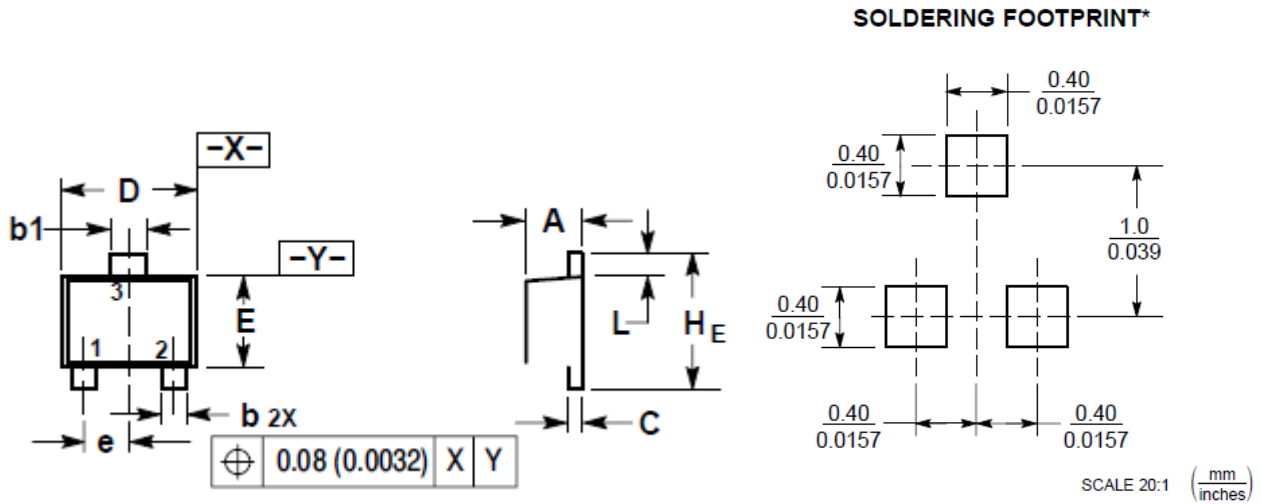
Figure 9. Safe Operating Area





**PACKAGE INFORMATION**

Dimension in SOT-723 (Unit: mm)



| DIM            | MILLIMETERS |       | INCHES    |        |
|----------------|-------------|-------|-----------|--------|
|                | MIN         | MAX   | MIN       | MAX    |
| A              | 0.450       | 0.550 | 0.018     | 0.022  |
| b              | 0.150       | 0.270 | 0.0059    | 0.0106 |
| b1             | 0.250       | 0.370 | 0.010     | 0.015  |
| C              | 0.070       | 0.170 | 0.0028    | 0.0067 |
| E              | 0.750       | 0.850 | 0.030     | 0.034  |
| e              | 0.400 BSC   |       | 0.016 BSC |        |
| H <sub>E</sub> | 1.150       | 1.250 | 0.045     | 0.049  |
| L              | 0.150       | 0.250 | 0.0059    | 0.0098 |



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